

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as indicated hereafter. It is believed that the following amendments and additions add no new matter to the present application.

In the Specification:

Please amend the paragraph [0032] starting on p. 8, line 7 as follows:

[0032] The enhanced QE image sensor of the present invention is shown in cross-section in FIG. 6. The image sensor comprises a photodiode formed by an N-well 12 in a p-substrate 10. (It will be understood that a P-photodiode could be formed by a P-well in an N-substrate). The photodiode underlies a STI region 16. The central portion of the STI region has been removed to form an opening exposing N-well 12. so that a stop layer 26, located at a bottom of the opening and at a top of the isolation region, directly overlies the photodiode. The stop layer preferably comprises silicon nitride or silicon oxynitride. An interlevel dielectric layer 28 overlies the stop layer and the substrate, thereby completing the image sensor.